

Molecular Structure:

Semiconducting chalcogenide glasses, first produced in the late 1950's, are normally classified as large covalently bonded network solids that act as a single molecular complex. They exhibit some unique optical and electrical properties.

Compositions:

The following are currently made in 5 inch and 17.40 mm diameter sizes for ULVAC systems.

- **GST** Germanium antimony telluride
- **SAG** Selenium arsenic germanium
- GAST Germanium arsenic selenium telluride
- **TAGS** Tellurium arsenic germanium silicon

Development:

In order to harness the extensive capabilities of this material, LTS is performing research and development for future applications with chalcogenide glass to:

- Improve the glass microstructure in chalcogenide targets for higher quality deposition,
- Develop a baseline process for commercial production and application of PRAM

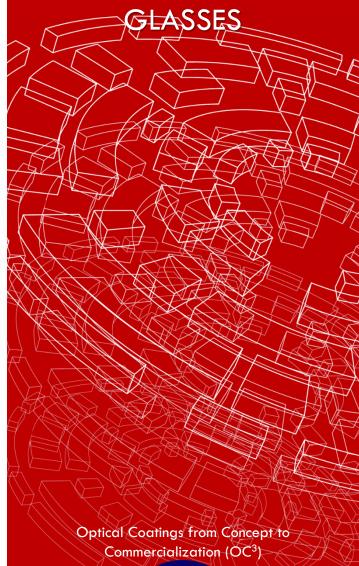
We welcome your inquiries and look forward to working with you on custom formulations Established in 1989 and based in New York, LTS has been pushing boundaries in the development and implementation of highpurity optical coating materials since its inception.

LTS produces high purity and high performance materials for the optics and fiberoptics, electronics, automotive, aerospace, medical, defense, crystal growth, and fuel cell industries, and are constantly developing new products and applications for our clients. We pride ourselves on our superb materials quality: whether it's a standard formulation or researching and developing new chemicals and compounds, we work to provide you with products unparalleled in their respective industries.

Our research and development team comprises experts in chemistry, chemical engineering, mechanical engineering, materials science, vacuum engineering, and high-caliber machining. Our production process is vertically integrated from raw materials procurement to the final finishing process, giving us precise control in creating materials to exact specifications.

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SEMICONDUCTING CHALCOGENIDE



Semiconducting Chalcogenide Glasses For Optics, Memory, & PRAM Applications

Applications:

Ultrafast broadband response times, tunable third-order nonlinear refractive index, and optical band gap energy make these materials useful for IR detectors, lenses, optical fibers, and photonic integrated circuits.

In addition to current storage technology, they are also used in emergent Phase Change memory (PRAM) development. An electric current pulse supplies the necessary heat to trigger the glassy-crystal phase transformation from amorphous to crystalline in a matter of nanoseconds. The read-out is performed by utilizing the relatively large differences in electrical resistance of the two phases. The crystalline region may be transformed back by a brief exposure to local heat followed by rapid cooling.

Optics:

Glass	<i>n</i> ₀	λ _{gap} (μm)	$n_2/n_2(SiO_2)$	FOM	Reference
Ge ₂₅ Se ₇₅	2.7	0.60	120	2	Lenz <i>et al.</i> (2000)*
Ge ₂₅ Se ₆₅ Te ₁₀	2.5	0.72	220	1	Lenz <i>et al.</i> (2000)*
Ge ₂₈ Se ₆₀ Sb ₁₂	2.61	0.69	360	3	Lenz et al. (2000)*
As ₄₀ Se ₆₀	2.78	0.70	500	2	Lenz <i>et al.</i> (2000)*
As ₄₀ Se ₆₀	2.81	0.70	930	11	Harbold <i>et al.</i> (2002a)
As ₃₉ Se ₆₁	2.81	0.70	660	4	Harbold et al. (2002a)
As ₄₀ Se ₅₅ Cu ₅	2.93	0.79	850	5	Harbold et al. (2002a)
As ₂₅ Se ₅₅ Te ₂₀	2.52	0.79	470	5	Harbold et al. (2002a)
As ₄₀ S ₆₀	2.45	0.52	220	>12	Harbold <i>et al.</i> (2002a)
As ₄₀ S ₅₀ Se ₁₀	2.49	0.55	380	4	Harbold <i>et al.</i> (2002a)
As ₄₀ S ₄₀ Se ₂₀	2.55	0.59	300	8	Harbold <i>et al.</i> (2002a)
As ₄₀ S ₃₀ Se ₃₀	2.62	0.62	430	5	Harbold et al. (2002a)
As ₄₀ S ₂₀ Se ₄₀	2.70	0.64	460	3	Harbold et al. (2002a)
As ₄₀ S ₁₀ Se ₅₀	2.76	0.67	560	7	Harbold et al. (2002a)
Ge _{15.38} As _{30.77} S _{53.85}		0.49	130	>21	Harbold et al. (2002b)
Ge _{15.38} As _{30.77} S _{32.31} Se _{21.54}		0.56	250	8.1	Harbold <i>et al.</i> (2002b)
Ge _{15.38} As _{30.77} S _{10.77} Se _{43.08}		0.61	390	11	Harbold et al. (2002b)
Ge ₂₀ As ₄₀ Se ₄₀		0.68	620	4.2	Harbold et al. (2002b)
Ge _{12.5} As ₂₅ Se _{62.5}		0.63	450	18	Harbold et al. (2002b)
Ge _{11.11} As _{22.22} Se _{66.67}		0.63	530	28	Harbold et al. (2002b)

*Measured at 1.5 μm.

Optical index, n_0 , and nonlinearities for chalcogenide glasses measured at 1.55 μ m.

QC Protocols:

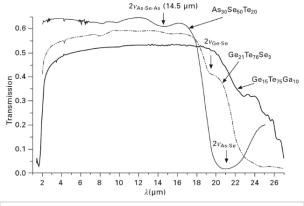
are agreed upon by the end-user. Typically LTS conducts the following four experiments to check the materials:

- Powder XRD to confirm the material is fully-reacted, and its amorphous state.
 - XRF to check the alloying ratio conforms to customer request.
- Optical microscopy on coupon to discern flaws.
- EDX on coupon to check local composition deviation.

We also offer pair distribution function analysis (based on EXAFS or x-ray diffraction PDF), ICP-AEM and ICP-MS, LECO, DTC, transport and optical measurements.

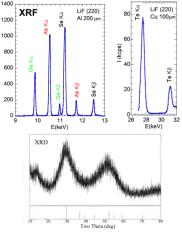


Transparency spectra of $As_{30}Se_{60}Te_{20}$, $Te_{76}Ge_{21}Se_{3}$, and $Te_{75}Ge_{15}Ga_{10}$ glasses (thickness is 2 mm).



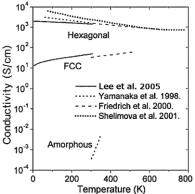
References:

Fairman, Ushkov - Chalcogenide Glasses Preparation, Properties and Applications (2014) Kolobove, Tominaga - Chalcogenides Metastability and Phase Change Phenomena (2012) A. Abdel-Wahab - Study of The Physical Properties of Some Semiconductor Materials (2012)



Electrical:

(kcps)



Above: Conductivity of Ge₂Sb₂Te₅ in different phases. The amorphous and FCC phases are both semiconducting, while the hexagonal phase is almost metallic.

Below: IV curves of a pair of 100 nm thick $In_x Sn_{20} Se_{60-x} Bi_{20}$ glass filaments undergoing phase change.

No data could be recorded during the ~10⁻⁹s change.

